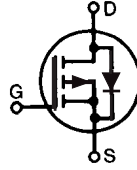


PolarP™ Power MOSFET
IXTC36P15P
IXTR36P15P
(Electrically Isolated Tab)

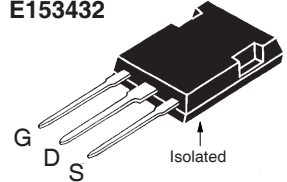
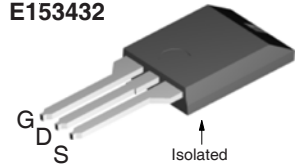
 P-Channel Enhancement Mode
 Avalanche Rated


$$V_{DSS} = -150V$$

$$I_{D25} = -22A$$

$$R_{DS(on)} \leq 120m\Omega$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $175^\circ C$	-150	V
V_{DGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GS} = 1M\Omega$	-150	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$	-22	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	-100	A
I_A	$T_C = 25^\circ C$	-36	A
E_{AS}	$T_C = 25^\circ C$	1.5	J
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 175^\circ C$	10	V/ns
P_D	$T_C = 25^\circ C$	150	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
V_{ISOL}	50/60 Hz, RMS, $t = 1$ minute	2500	V~
F_C	Mounting Force (ISOPLUS220)	11..65 / 25..14.6	N/lb
F_C	Mounting Force (ISOPLUS247)	20..120 / 4.5..27	N/lb
Weight	ISOPLUS220	2	g
	ISOPLUS247	5	g

ISOPLUS247 (IXTR)
 E153432

ISOPLUS220 (IXTC)
 E153432

 G = Gate D = Drain
 S = Source

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 2500V~ Electrical Isolation
- Avalanche Rated
- Extended FBSOA
- Fast Intrinsic Diode
- Low $R_{DS(ON)}$ and Q_G

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High-Side Switching
- Push Pull Amplifiers
- DC Choppers
- Automatic Test Equipment
- Current Regulators
- Battery Charger Applications

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = -250\mu A$	-150		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	-3.0		-5.0 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 150^\circ C$			-10 μA -250 μA
$R_{DS(on)}$	$V_{GS} = -10V$, $I_D = -18A$, Note 1			120 m Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = -10\text{V}$, $I_D = -18\text{A}$, Note 1	11	19	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = -25\text{V}$, $f = 1\text{MHz}$		2950	pF
C_{oss}			615	pF
C_{rss}			115	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = -10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = -18\text{A}$ $R_G = 5\Omega$ (External)		28	ns
t_r			37	ns
$t_{d(off)}$			45	ns
t_f			14	ns
$Q_{g(on)}$	$V_{GS} = -10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = -18\text{A}$		55	nC
Q_{gs}			21	nC
Q_{gd}			20	nC
R_{thJC}				1.00 $^\circ\text{C/W}$
R_{thCS}		0.15		$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_s	$V_{GS} = 0\text{V}$			-36 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			-100 A
V_{SD}	$I_F = -18\text{A}$, $V_{GS} = 0\text{V}$, Note 1			-3.0 V
t_{rr}	$I_F = -25$, $-di/dt = -100\text{A}/\mu\text{s}$ $V_R = -100\text{V}$, $V_{GS} = 0\text{V}$		150	ns
Q_{RM}			2.0	μC

Note 1: Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

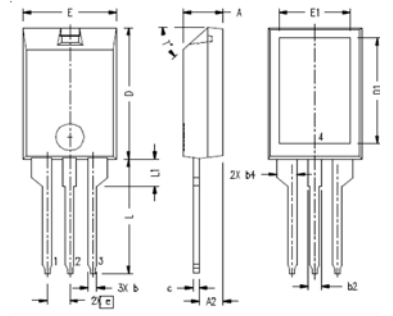
PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2
4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

ISOPLUS220™ Outline

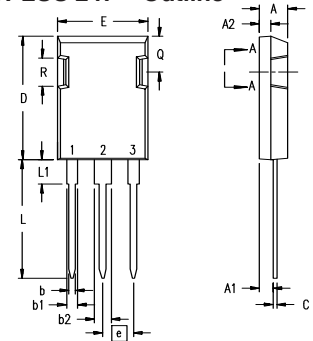


Note:
Bottom heatsink (Pin 4) is electrically isolated from Pin 1, 2, or 3.

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.157	.197	4.00	5.00
A2	.098	.118	2.50	3.00
b	.035	.051	0.90	1.30
b2	.049	.065	1.25	1.65
b4	.093	.100	2.35	2.55
c	.028	.039	0.70	1.00
D	.591	.630	15.00	16.00
D1	.472	.512	12.00	13.00
E	.394	.433	10.00	11.00
E1	.295	.335	7.50	8.50
e	.100 BASIC		2.55 BASIC	
L	.512	.571	13.00	14.50
L1	.118	.138	3.00	3.50
T*			42.5*	47.5*

Ref: IXYS CO 0177 R0

ISOPLUS 247™ Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190



Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.